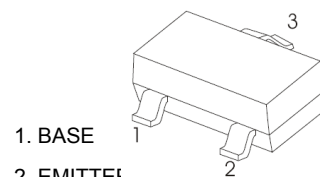


TRANSISTOR(PNP)

FEATURES

- Complimentary to S8050
- Collector current: $I_C=0.5A$

SOT-23



1. BASE
2. EMITTER
3. COLLECTOR

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

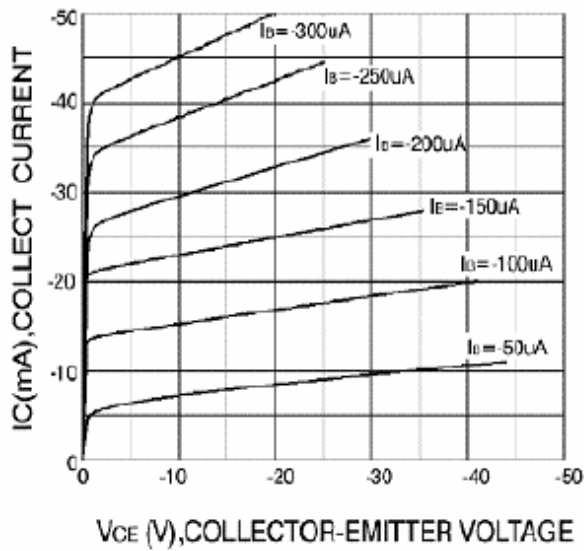
Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-0.5	A
P_C	Collector Power Dissipation	0.3	W
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55-150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

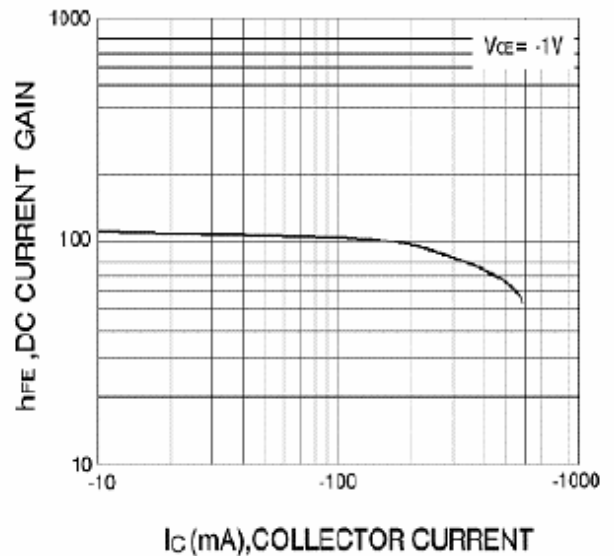
Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}, I_E=0$	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, I_B=0$	-25		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu\text{A}, I_C=0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB} = -40\text{V}, I_E=0$		-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -20\text{V}, I_B=0$		-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -3\text{V}, I_C=0$		-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -1\text{V}, I_C = -50\text{mA}$	120	400	
	$h_{FE(2)}$	$V_{CE} = -1\text{V}, I_C = -500\text{mA}$	50		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500\text{mA}, I_B = -50\text{mA}$		-0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500\text{mA}, I_B = -50\text{mA}$		-1.2	V
Transition frequency	f_T	$V_{CE} = -6\text{V}, I_C = -20\text{mA}$ $f=30\text{MHz}$	150		MHz

CLASSIFICATION OF $h_{FE(1)}$

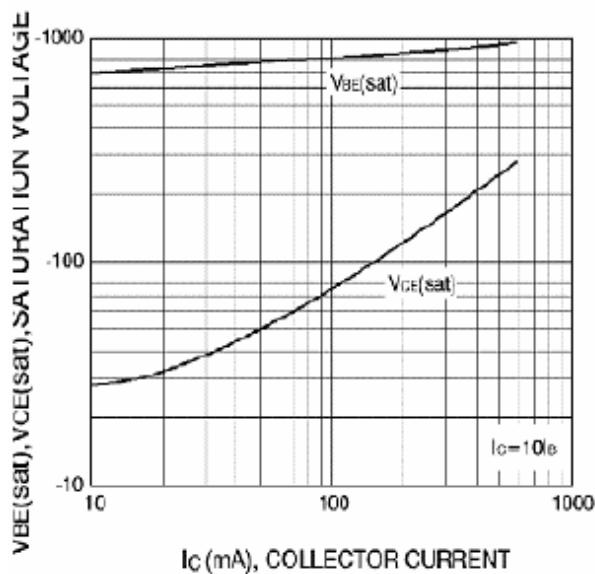
Rank	L	H
Range	120-200	200-350



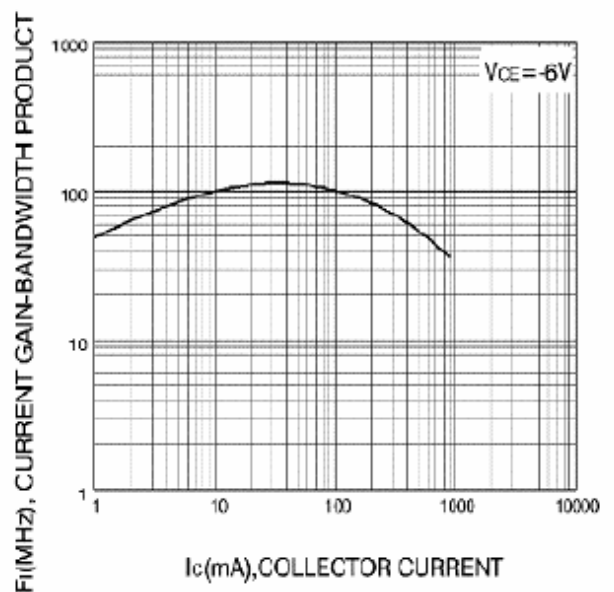
Static Characteristic



DC current Gain



**Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage**



Current Gain Bandwidth Product